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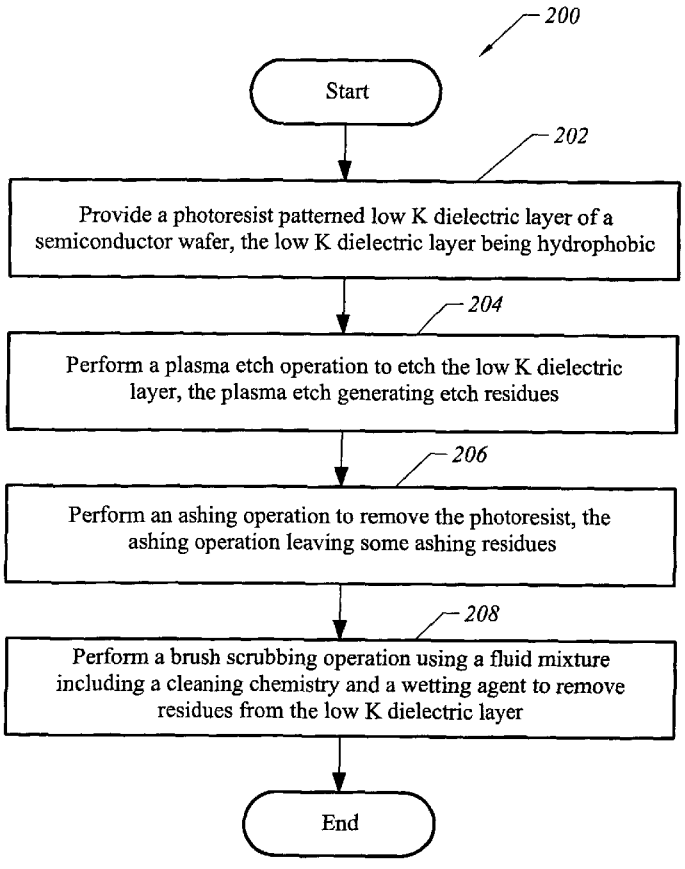
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(54) Title: METHOD FOR POST-ETCH AND STRIP RESIDUE REMOVAL ON CORAL FILMS



(57) Abstract: A method for cleaning a semiconductor wafer is provided which includes plasma etching a feature into a low K dielectric layer having a photoresist mask where the plasma etching generates etch residues (Fig.4, 204). The method also includes ashing the semiconductor wafer to remove the photoresist mask where the ashing generating ashing residues (Fig.4, 206). The method further includes removing the etching residues and the ashing residues from the low K dielectric layer where the removing is enhanced by scrubbing the low K dielectric layer of the semiconductor wafer with a wet brush that applies a fluid mixture including a cleaning chemistry and a wetting agent Fig.4, 208).

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